Vishay Semiconductors

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Hyperfast Rectifier, 8 A FRED Pt®



TO-220 FullPAK 2L

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I _{F(AV)}	8 A				
V _R	600 V				
V _F at I _F	1.3 V				
t _{rr} (typ.)	16 ns				
T _J max.	175 °C				
Package	TO-220 FullPAK 2L				
Circuit configuration	Single				

FEATURES

- Hyperfast soft recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- True 2 pin package
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

MECHANICAL DATA

Case: TO-220 FullPAK 2L

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V _{RRM}		600	V
Average rectified forward current in DC	I _{F(AV)}	T _C = 114 °C	8	
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	80	А
Repetitive peak surge current Square wave 20 kHz duty cycle (50 %)	I _{FRM}	T _C = 96 °C	16	
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	600	-	-		
Forward voltage	V	I _F = 8 A	-	2.0	2.65	V	
	V _F	I _F = 8 A, T _J = 150 °C	-	1.3	1.85		
Povero lockage ourrent	I	$V_{R} = V_{R}$ rated	-	0.02	12		
Reverse leakage current		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	15	100	μA	
Junction capacitance	CT	V _R = 600 V	-	6	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH	

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DYNAMIC RECOVERY CHARACTERISTICS (T_J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	TEST CONDITIONS			MAX.	UNITS
		$I_F = 1 \text{ A}, \ dI_F/dt = 100$	A/ μ s, V _R = 30 V	-	16	23	
Reverse recovery time	+	$I_F = 8 \text{ A}, \ dI_F/dt = 100$	I _F = 8 A, dI _F /dt = 100 A/μs, V _R = 30 V			28	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	21	-	ns
		T _J = 125 °C	I _F = 8 A, dI _F /dt = 200 A/µs, V _B = 390 V	-	39	-	
Peak recovery current	1	T _J = 25 °C		-	3	-	A nC
Feak recovery current	I _{RRM}	T _J = 125 °C		-	5	-	
	0	T _J = 25 °C		-	36	-	
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	108	-	
Reverse recovery time	t _{rr}		I _F = 8 A,	-	30	-	ns
Peak recovery current	I _{RRM}	T _J = 125 °C	$dI_F/dt = 600 A/\mu s,$	-	13	-	A
Reverse recovery charge	Q _{rr}		V _R = 390 V	-	205	-	nC

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C	
Thermal resistance, junction-to-case	R _{thJC}		-	4.6	5.5		
Thermal resistance, junction-to-ambient	R _{thJA}	Typical socket mount	-	-	70	°C/W	
Typical thermal resistance, case-to-heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-		
Woight			-	2	-	g	
Weight			-	0.07	-	oz.	
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-220 FullPAK 2L		ETH0	806FP		



VS-ETH0806FP-M3

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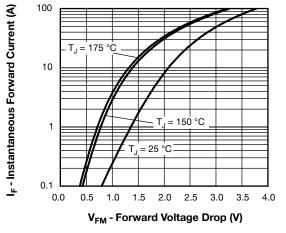


Fig. 1 - Typical Forward Voltage Drop Characteristics

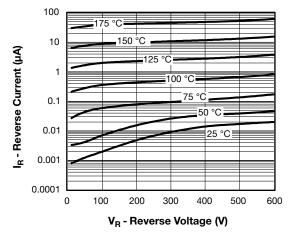


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

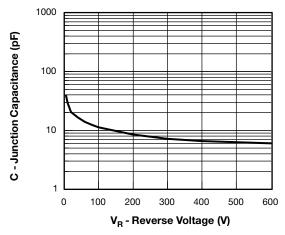


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

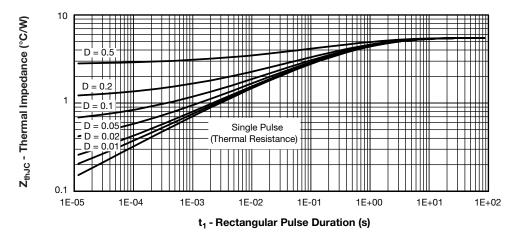
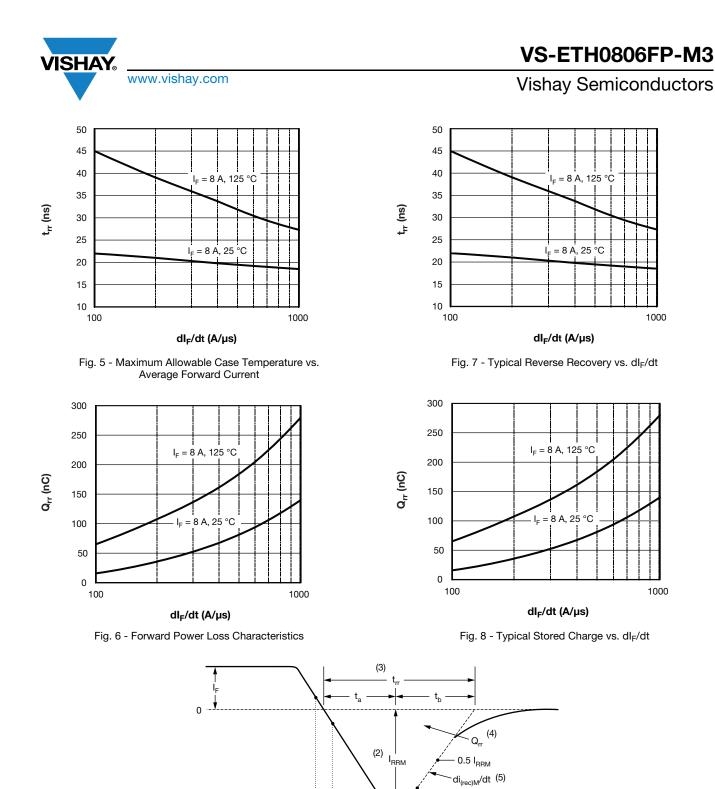


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

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(1) di_F/dt

(1) di_F/dt - rate of change of current

(2) I_{RRM} - peak reverse recovery current (3) t_{rr} - reverse recovery time measured

from zero crossing point of negative

going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

through zero crossing

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Fig. 9 - Reverse Recovery Waveform and Definitions

0.75 I_{RRM}

and I_{RRM}

(4) Q_{rr} - area under curve defined by t_{rr}

(5) $di_{(rec)M}/dt$ - peak rate of change of

current during t_b portion of t_{rr}

 $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{T}$

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ORDERING INFORMATION TABLE

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Device code	vs-	Е	т	н	08	06	FP	-M3
				<u> </u>				
		2	3	4	5	6	7	8
	1 -	- Visl	nay Sem	niconduo	ctors pr	oduct		
	2 -	Circ	cuit cont	figuratio	n:			
		E =	single					
	3 -	• T =	TO-220)				
	4 -	• H=	hyperfa	ast recov	very tim	е		
	5 -	- Cur	rent coo	de: 08 =	8 A			
	6 -	· Vol	tage coo	de: 06 =	600 V			
	7 -	FP :	= TO-22	0 FullPA	AK 2L			
	8 -	· Env	ironmer	ntal digit				
		-M3	3 = halog	gen-free	, RoHS	-compli	ant, and	d termir

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER TUBE MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-ETH0806FP-M3	50	1000	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?96157				
Part marking information	www.vishay.com/doc?95392				
SPICE model	www.vishay.com/doc?96865				



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